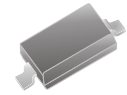


## CDSV16-G

### RoHS Device

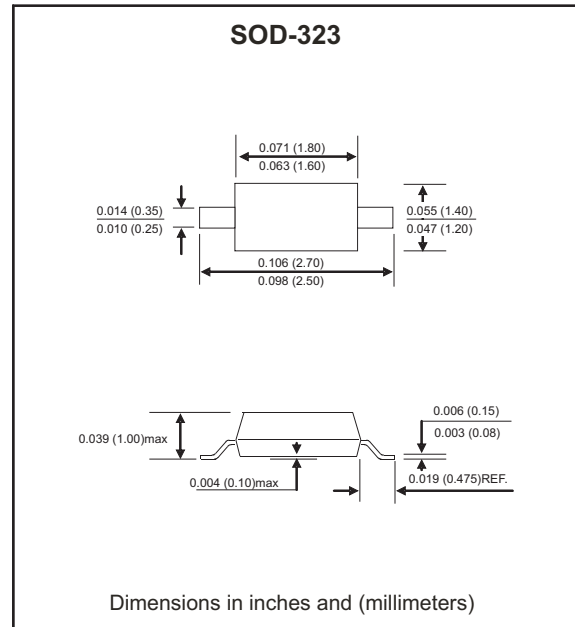


### Features

- Fast Switching Speed
- Electrically Identical to Standard JEDEC
- High Conductance
- Surface Mount Package Ideally Suited for Automatic Insertion
- Flat Package SOD-123 in Stead mini-MELF Package

### Mechanical data

- Case: SOD-323, Molded Plastic
- Terminals: Solderable per MIL-STD-202, Method 208
- Weight: 0.01 gram(approx.)



### Maximum Rating (at Ta=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Max	Unit
Non-Repetitive peak reverse voltage		V <sub>RM</sub>		100	V
Peak repetitive peak reverse voltage Working peak reverse voltage DC blocking voltage		V <sub>RRM</sub> V <sub>VRM</sub> V <sub>R</sub>		75	V
RMS reverse voltage		V <sub>R(RMS)</sub>		53	V
Forward continuous current		I <sub>FM</sub>		300	mA
Average rectified output current		I <sub>o</sub>		150	mA
Peak forward surge current	T <sub>P</sub> = 1μS T <sub>P</sub> = 1S	I <sub>FSM</sub>		2 1	A
Power dissipation		P <sub>d</sub>		200	mW
Thermal Resistance (Junction to ambient)		R <sub>θJA</sub>		625	°C/W
Storage temperature		T <sub>STG</sub>	-65	+150	°C
Junction temperature		T <sub>j</sub>		+125	°C

### Electrical Characteristics (at Ta=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	I <sub>F</sub> = 1 mA DC I <sub>F</sub> = 10mA DC I <sub>F</sub> = 50mA DC I <sub>F</sub> = 150mA DC	V <sub>F</sub>			0.715 0.855 1.0 1.25	V
Reverse current	V <sub>R</sub> = 20 V V <sub>R</sub> = 75 V	I <sub>R</sub>			25 1	nA μA
Capacitance between terminals	f = 1 MHz, and 0VDC reverse voltage	C <sub>T</sub>			2	pF
Reverse recovery time	I <sub>F</sub> = I <sub>R</sub> = 10 mA, R <sub>L</sub> = 100 ohms, I <sub>rr</sub> = 0.1 X I <sub>R</sub>	T <sub>RR</sub>			4	nS

## Typical Characteristics (CDSV16-G)

Fig.1 - Forward Characteristics

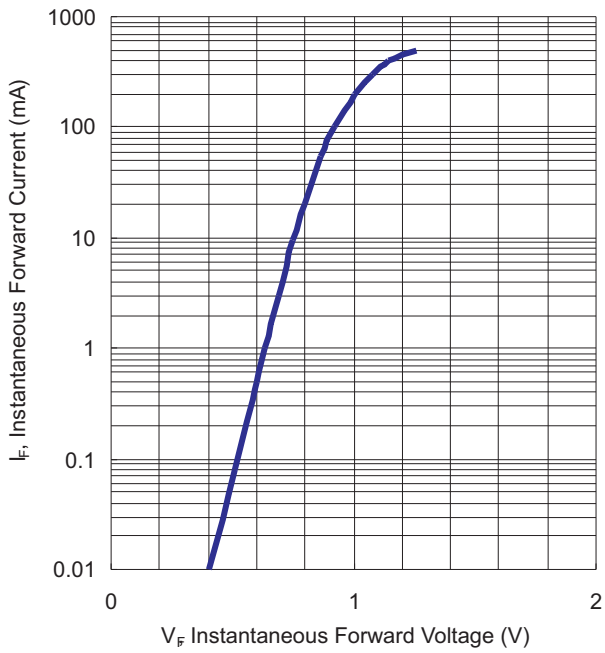


Fig.2 - Leakage current V.S. Junction Temperature

